

SCT4045DW7HR

Automotive Grade N-channel SiC power MOSFET

Datasheet

V_{DSS}	750V
R _{DS(on)} (Typ.)	45mΩ
I _D *1	31A
P_D	93W

TO-263-7L

Features

- 1) Qualified to AEC-Q101
- 2) Low on-resistance
- 3) Fast switching speed
- 4) Fast reverse recovery
- 5) Easy to parallel
- 6) Simple to drive
- 7) Pb-free lead plating; RoHS compliant

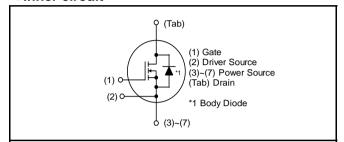
Application

- Automobile
- Switch mode power supplies

Outline



Inner circuit



Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.

Packaging specifications

	Packing	Embossed tape
	Reel size (mm)	330
Typo	Tape width (mm)	24
Type	Basic ordering unit (pcs)	1000
	Taping code	TL
	Marking	SCT4045DW7

● **Absolute maximum ratings** (T_{vi} = 25°C unless otherwise specified.)

Parameter		Symbol	Value	Unit	
Drain - source voltage		V_{DSS}	750	V	
Continuous drain	$V_{GS} = V_{GS_{on}}$	$T_c = 25^{\circ}C$	I _D , I _S *1	31	А
and source current	V _{GS} = V _{GS_on}	T _c = 100°C	I _D , I _S	22	А
Pulsed drain current	$V_{GS} = V_{GS_on}$	$T_c = 25^{\circ}C$	I _{D,pulse} *2	61	А
Body diode pulsed forward	ard current	$T_c = 25^{\circ}C$	I _{S,pulse} *1,*3	31	А
Body diode surge forward current V		$V_{GS} = 0 V$	I _{S,pulse} *1,*4	61	А
Gate - source voltage (DC)		V_{GSS_DC}	-4 to +21	V	
Gate - source surge voltage (t _{surge} < 300ns)		V _{GSS_surge} *5	-4 to +23	V	
Recommended turn-on gate - source drive voltage		ive voltage	$V_{GS_on}^{*6}$	+15 to +18	V
Recommended turn-off gate - source drive voltage		V_{GS_off}	0	V	
Virtual junction temperature			T_{vj}	175	°C
Range of storage temperature		T_{stg}	-40 to +175	°C	

ullet Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	itions		Values		
raiailletei			Min.	Тур.	Max.	Unit	
Drain - Source breakdown voltage	W	$V_{GS} = 0 \text{ V}, I_D = 5.3 \text{mA}$				V	
	V (BR)DSS	$T_{vj} = 25^{\circ}C$	750	-	-	V	
		$V_{GS} = 0 \text{ V}, V_{DS} = 750 \text{V}$					
Zero Gate voltage Drain current	I _{DSS}	$T_{vj} = 25^{\circ}C$	-	1	80	μΑ	
Diam ourion		T _{vj} = 150°C	-	10	-		
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +21V , V_{DS} = 0V$	-	-	100	nA	
Gate - Source leakage current		$V_{GS} = -4V$, $V_{DS} = 0V$	-	-	-100	nA	
Gate threshold voltage	$V_{GS(th)}^{*7}$	$V_{DS} = 10V, I_{D} = 8.89 \text{mA}$	2.8	ı	4.8	V	
		$V_{GS} = 18V, I_{D} = 17A$					
Static Drain - Source on - state resistance	R _{DS(on)} *8	$T_{vj} = 25^{\circ}C$	-	45	59	mΩ	
		T _{vj} = 150°C	-	77	-		
Gate input resistance	R_{G}	f = 1MHz, open drain	-	4	-	Ω	

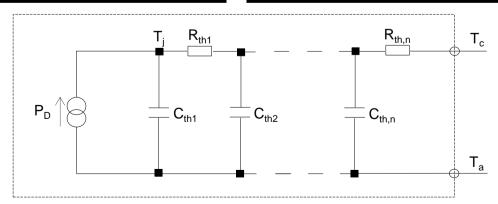
●Thermal resistance

Parameter	Symbol	Values			Unit
Falametei		Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	$R_{thJC}^{^{*9}}$	-	1.2	1.6	K/W

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	8.9 × 10 ⁻²	
R _{th2}	5.7 ×10 ⁻¹	K/W
R _{th3}	5.3 ×10 ⁻¹	

Symbol	Value	Unit
C _{th1}	5.3 ×10 ⁻⁴	
C_{th2}	2.8 × 10 ⁻³	Ws/K
C _{th3}	1.5 ×10 ⁻¹	



ullet Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

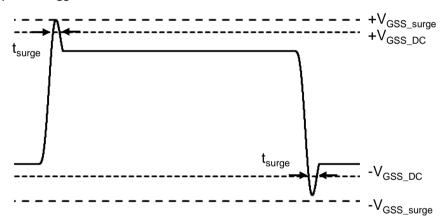
Doromotor	Cymah al	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Transconductance	g fs *8	$V_{DS} = 10V, I_{D} = 17A$	-	9.3	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	1460	-	
Output capacitance	C _{oss}	V _{DS} = 500V	-	69	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	5	-	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V \text{ to } 500V$	-	90	-	pF
Total Gate charge	Q _g *8	$V_{DS} = 500V$ $I_{D} = 17A$	ı	63	-	
Gate - Source charge	Q _{gs} *8	$V_{GS} = 18V$	ı	14	ı	nC
Gate - Drain charge	Q _{gd} *8	See Fig. 1-1, 1-2.	ı	19	-	
Turn - on delay time	t _{d(on)} *8	$V_{DS} = 500V$	ı	5.1	ı	
Rise time	t _r *8	$I_D = 17A$ $V_{GS} = +18V / 0V$	1	16	-	ns
Turn - off delay time	t _{d(off)} *8	$R_G = 3.3\Omega$, L = 250µH E_{on} includes diode	-	27	-	113
Fall time	t _f *8	reverse recovery $L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF	1	10	-	
Turn - on switching loss	E _{on} *8	See Fig. 2-1, 2-2, 2-3.	ı	112	1	μJ
Turn - off switching loss	E _{off} *8		ı	17	-	μυ
$V_{GS(on)} = +15$	/ _ t _{sc} *9	$V_{DS} \le 400V$ $V_{DS,peak} \le 750V$	-	12.0	-	μs
withstand time $V_{GS(on)} = +18V$		$T_{vj(start)} = 25$ °C $R_G = 2.2\Omega$	-	11.5	-	μs

●Body diode electrical characteristics (Source-Drain) (T_{vi} = 25°C unless otherwise specified)

Dorometer	Symbol Conditions -	Values			l lm:t	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward voltage	V _{SD} *8	$V_{GS} = 0V, I_{S} = 17A$	ı	3.3	ı	V
Reverse recovery time	t _{rr} *8	$I_F = 17A$ $V_R = 500V$	ı	9.3	ı	ns
Reverse recovery charge	Q _{rr} *8	di/dt = 2900A/µs	ı	89	ı	nC
Peak reverse recovery current	I _{rrm} *8	$L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF See Fig. 3-1, 3-2.	ı	19	ı	А

^{*1} Limited by maximum T_{vi} and for Max. R_{thJC} .

*5 Example of acceptable V_{GS} waveform



Please note especially when using driver source that V_{GSS_surge} must be in the range of absolute maximum rating.

- *6 Please be advised not to use SiC-MOSFETs with V_{GS} below 10V as doing so may cause thermal runaway.
- *7 Tested after applying $V_{GS} = 21V$ for 100ms.
- *8 Pulsed
- *9 The value is based on TO-247 package. Single Pulsed.
- *10 Measured conformable to JESD51-14.

See the application note "rthjc_measurement_and_usage_an-e.pdf". Link

URL: https://fscdn.rohm.com/en/products/databook/applinote/discrete/common/rthjc_measurement_and_usage_an-e.pdf

4/15

^{*2} Pulse width and duty cycle are limited by T_{vj,max}.

^{*3} Only for body-diode, Repititive pulse, PW ≤ 1.5µs, Duty cycle ≤ 5%

^{*4} When used as a protective function, PW ≤ 10µs

Fig.1 Power Dissipation Derating Curve

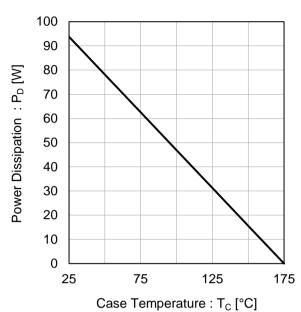


Fig.2 Maximum Safe Operating Area

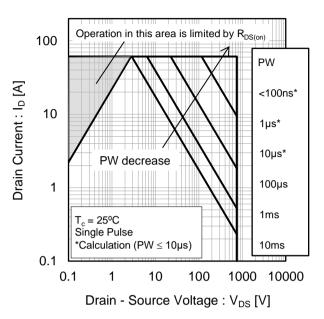
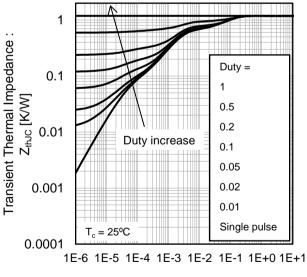


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width



Pulse Width: PW [s]

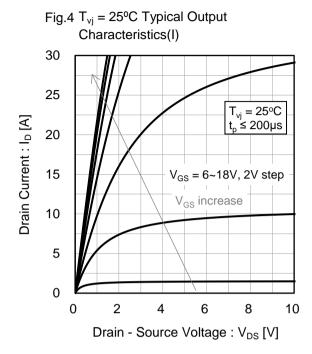
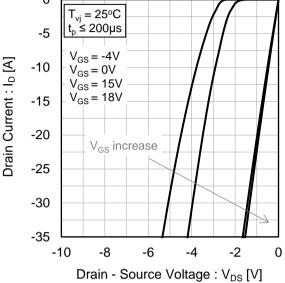
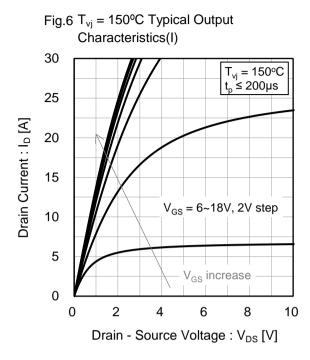
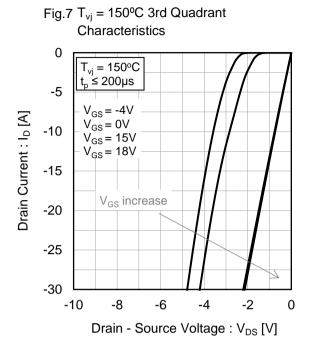


Fig.5 $T_{vj} = 25^{\circ}$ C 3rd Quadrant Characteristics



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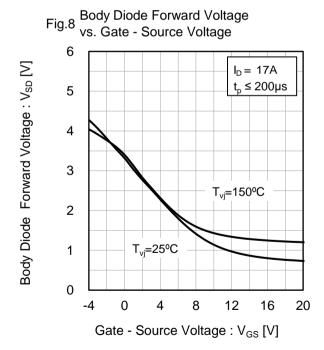


Fig.9 Typical Transfer Characteristics (I)

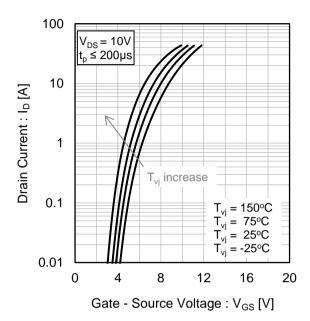


Fig.10 Typical Transfer Characteristics (II)

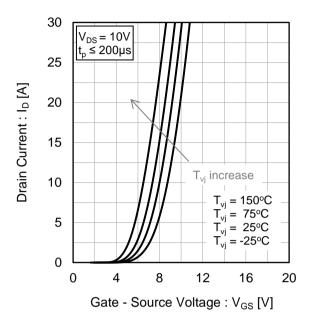


Fig.11 Gate Threshold Voltage vs. Virtual Junction Temperature

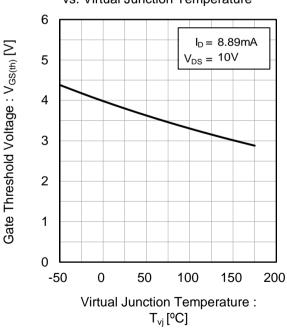


Fig.12 Transconductance vs. Drain Current

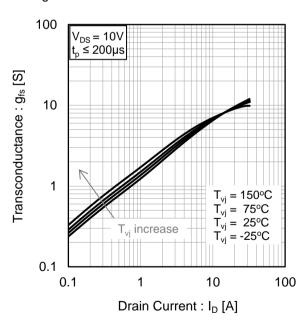


Fig.13 Static Drain - Source On - State Resistance vs. Gate - Source Voltage

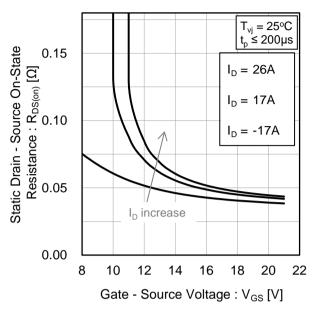


Fig.14 Static Drain - Source On - State Resistance vs. Virtual Junction Temperature

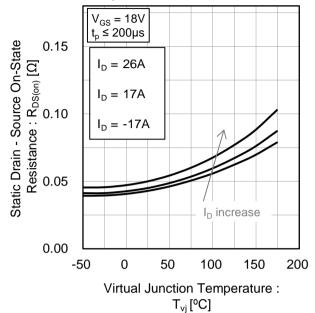


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current

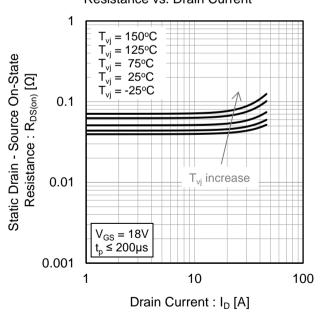
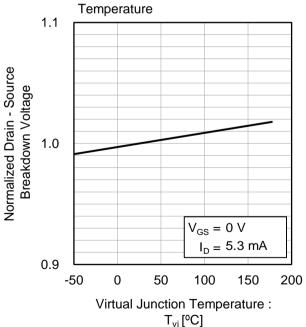
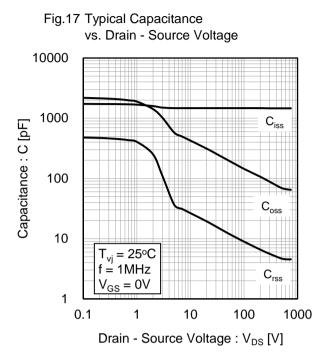


Fig.16 Normalized Drain - Source Breakdown Voltage vs. Virtual Junction





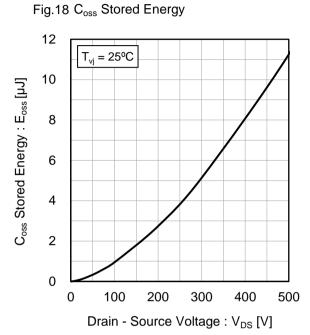
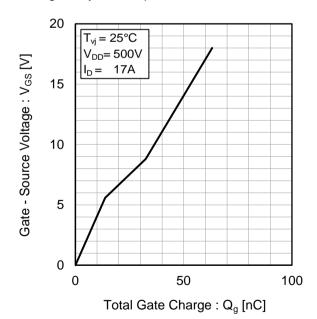


Fig.19 Dynamic Input Characteristics



20

0

0

•Electrical characteristic curves

Fig.20 Typical Switching Time

vs. External Gate Resistance 80 $T_{vi} = 25^{\circ}C$ $I_D =$ 17A V_{DD}= 500V 60 V_{GS}= +18V/0V Switching Time: t [ns] $L = 250 \mu H$ 40 $t_{\rm r}$

External Gate Resistance : $R_G[\Omega]$

10

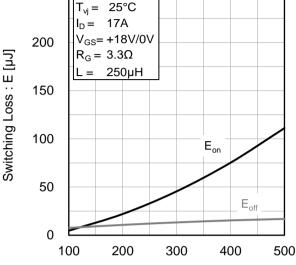
 $t_{d(on)}$

15

20

vs. Drain - Source Voltage 250 $T_{v_i} = 25^{\circ}C$ $I_D =$ 17A V_{GS}= +18V/0V 200

Fig.21 Typical Switching Loss



Drain - Source Voltage : V_{DS} [V]

Fig.22 Typical Switching Loss vs. Drain Current

5

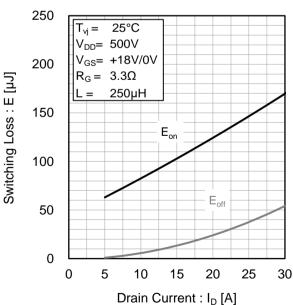
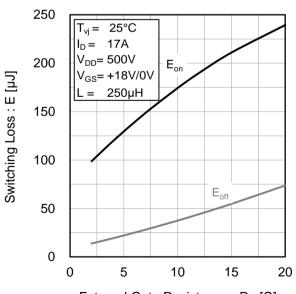


Fig.23 Typical Switching Loss vs. External Gate Resistance



External Gate Resistance : $R_G[\Omega]$

Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

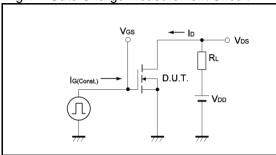


Fig.2-1 Switching Characteristics Measurement Circuit

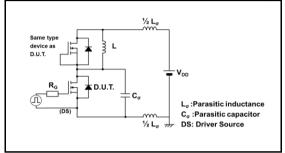


Fig.2-3 Waveforms for Switching Energy Loss

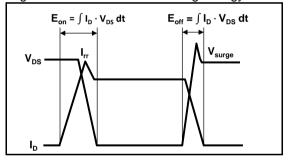


Fig.3-1 Reverse Recovery Time Measurement Circuit

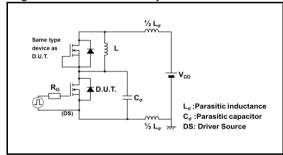


Fig.1-2 Gate Charge Waveform

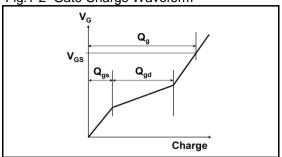


Fig.2-2 Waveforms for Switching Time

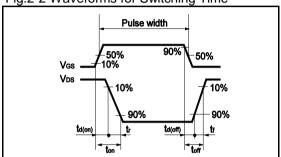
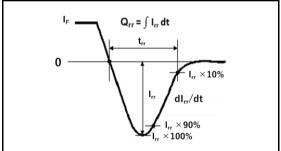
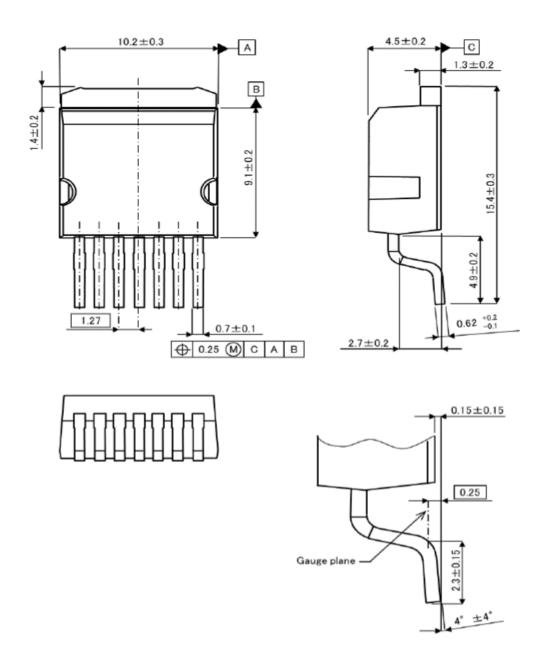


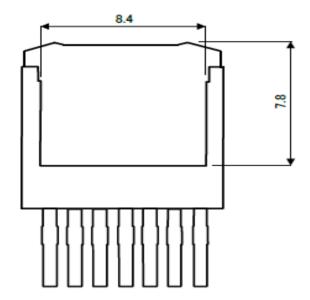
Fig.3-2 Reverse Recovery Waveform



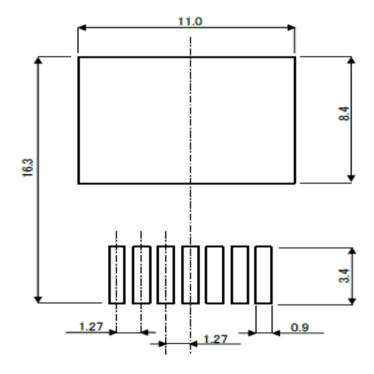
●Package Dimensions



Unit: mm



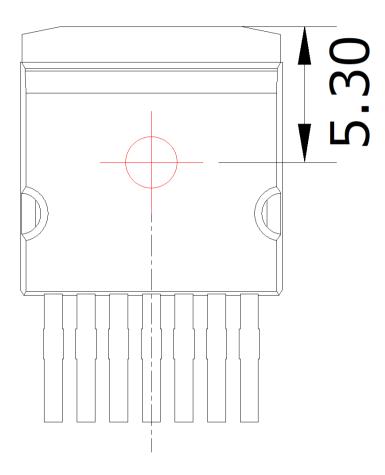
RECOMMENDED FOOTPRINT DIMENSIONS



Unit: mm

●Die Bonding Layout





- •Front view of the packaging.
- •Dimensions are design values.
- ·If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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